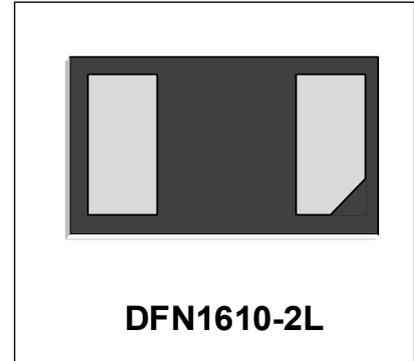




## Features

- Small Body Outline Dimensions:  
0.063" x 0.040" (1.6 mm x 1.0 mm)
- Protects one I/O or power line
- Low Clamping Voltage
- Working Voltage: 18V
- Low Leakage Current



## IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 30\text{kV}$  (air),  $\pm 30\text{kV}$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 45A (8/20 $\mu\text{s}$ )

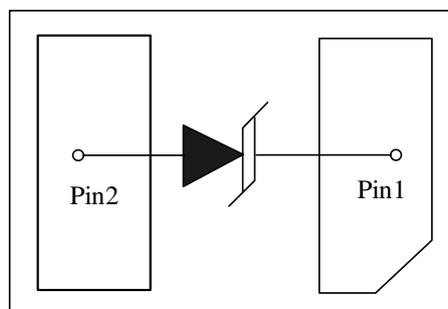
## Mechanical Characteristics

- DFN1610-2L package
- Marking: Marking Code
- Packaging: Tape and Reel per EIA 481
- RoHS Compliant

## Applications

- Laptop Computers
- Cellular Phones
- Digital Cameras
- Personal Digital Assistants (PDAs)

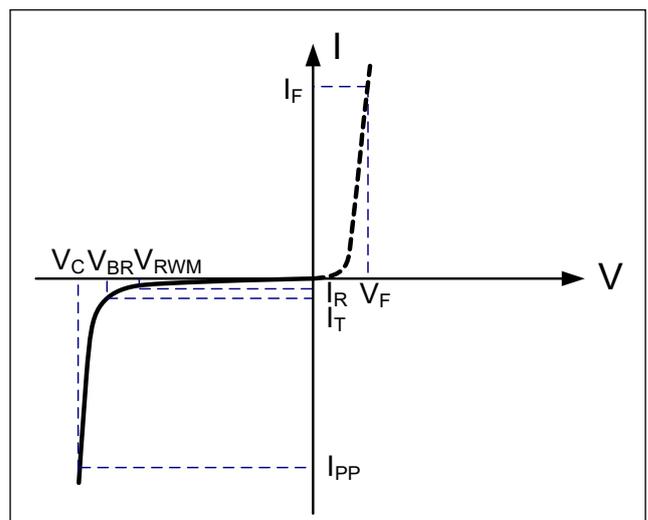
## Schematic & PIN Configuration



<b>Absolute Maximum Rating</b>			
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	1620	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{PP}$	45	A
Operating Temperature	$T_J$	-55 to + 125	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$

### Electrical Parameters (T=25 $^{\circ}C$ )

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Reverse Stand-Off Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Reverse Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



### Electrical Characteristics

<b>DW18DP-S</b>						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				18	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T = 1mA$	20			V
Reverse Leakage Current	$I_R$	$V_{RWM} = 18V, T = 25^{\circ}C$			500	nA
Forward Voltage	$V_F$	$I_F = 10mA$	0.5		1	V
Clamping Voltage	$V_C$	$I_{PP} = 45A, t_p = 8/20\mu s$		33	36	V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 4A$ $t_p = 0.2/100ns$		22		V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 16A$ $t_p = 0.2/100ns$		23.2		V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	TLP=0.2/100ns		0.1		$\Omega$
Junction Capacitance	$C_j$	$V_R = 0V, f = 1MHz$		250	350	pF

**Note:** 1、TLP Setting :  $t_p = 100ns, t_r = 0.2ns, I_{TLP}$  and  $V_{TLP}$  sample window:  $t_1 = 70ns$  to  $t_2 = 90ns$ .

2、Dynamic resistance calculated from  $I_{PP} = 4A$  to  $I_{PP} = 16A$  using "Best Fit".

Ver.: A1 2019-02-22 WA

## Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

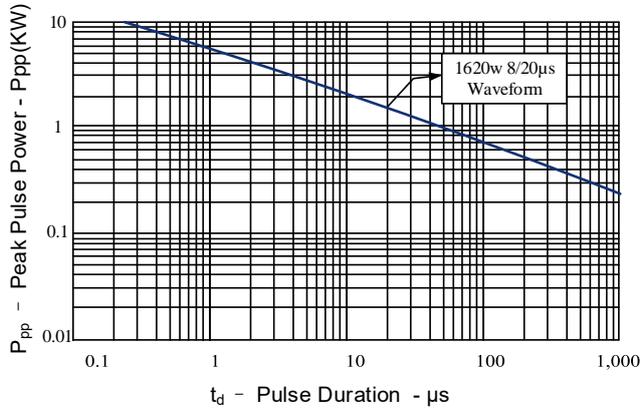


Figure 2: Power Derating Curve

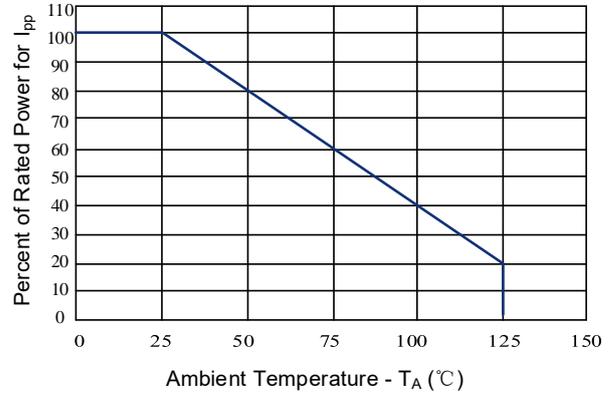


Figure 3: Clamping Voltage vs. Peak Pulse Current

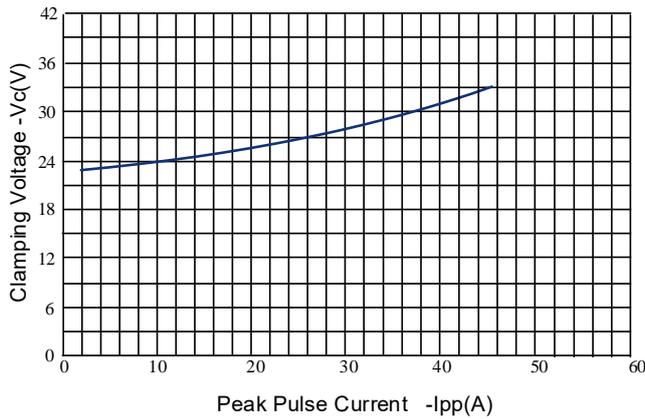


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

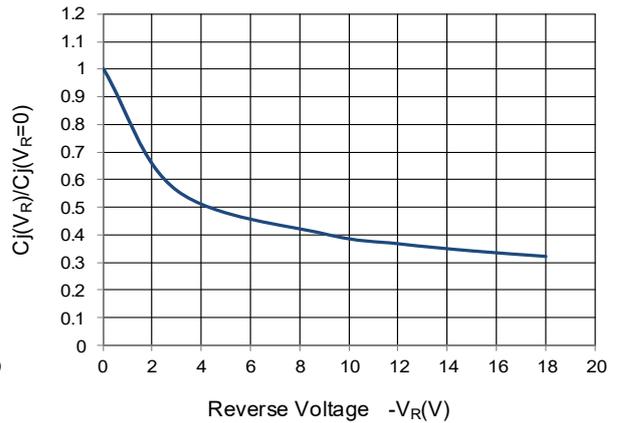


Figure 5: 8/20μs Pulse Waveform

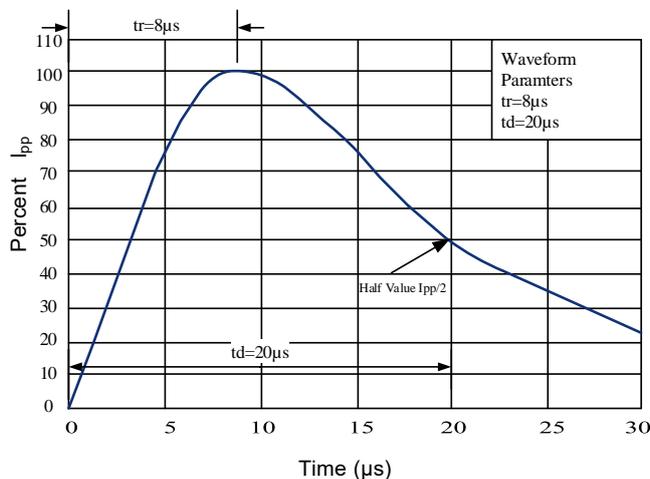
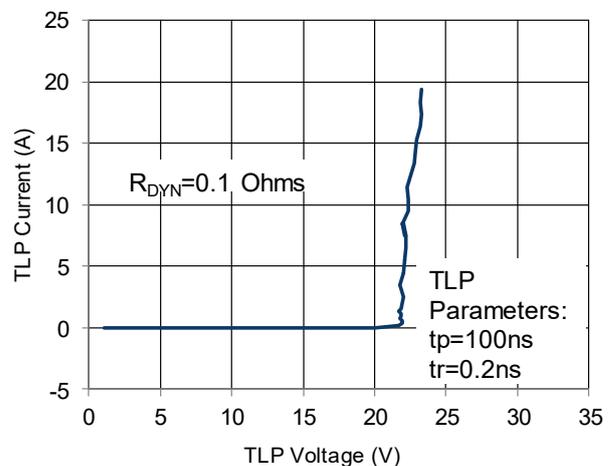


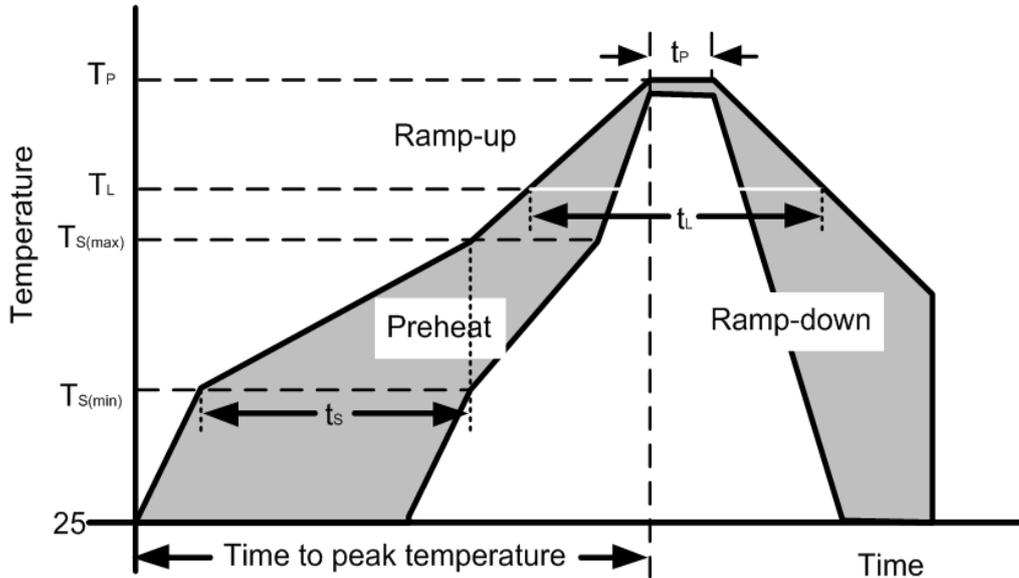
Figure 6: TLP I-V Curve



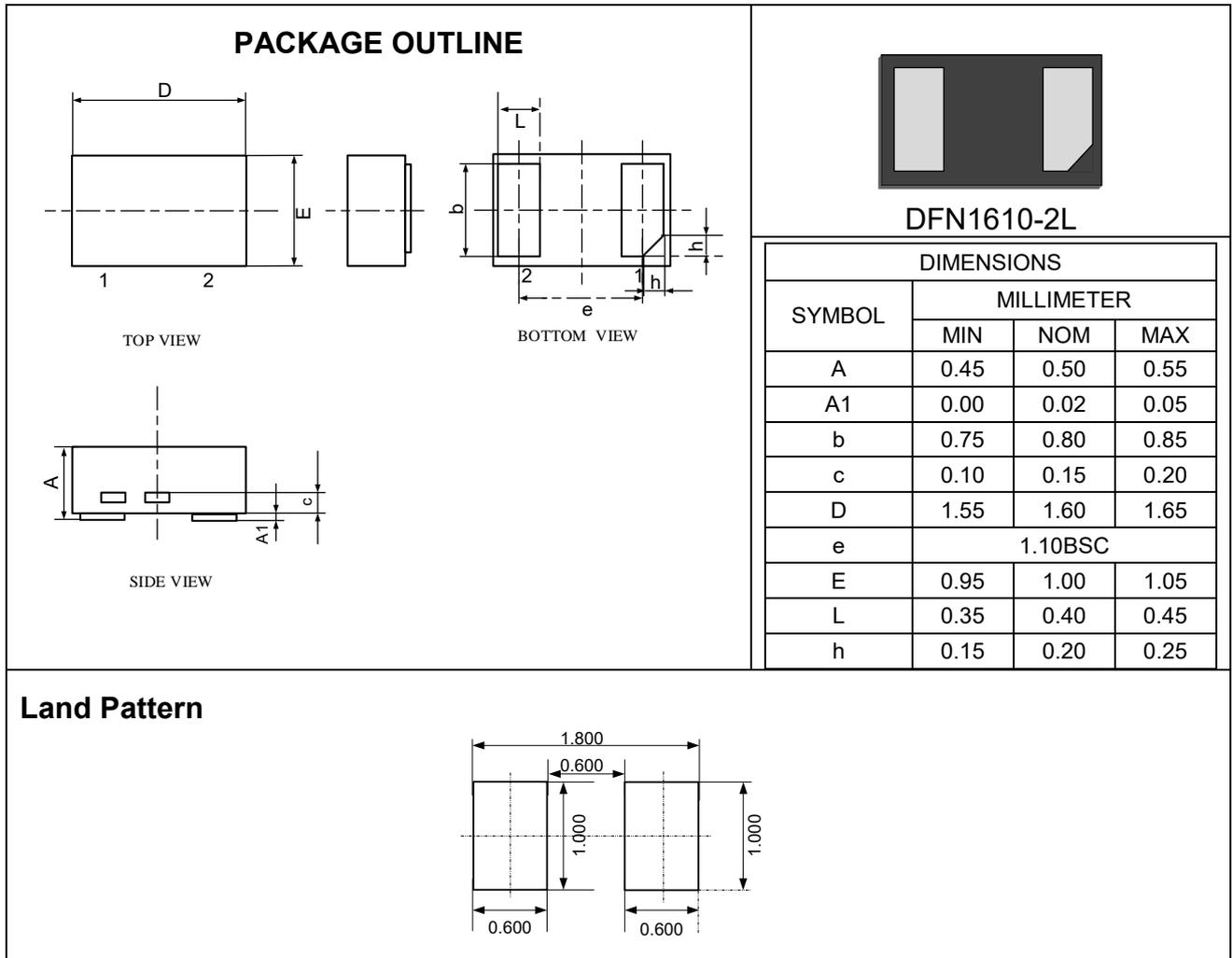


## Soldering Parameters

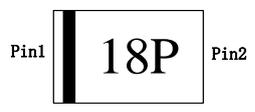
Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{S(min)}$ )	150°C
	Temperature Max ( $T_{S(max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{S(max)}$ to $T_L$ —Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_P$ )		260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C



## Outline Drawing –DFN1610-2L



## Marking Codes

Part Number	Marking Code
DW18DP-S	

## Package Information

Qty: 3k/Reel